

Hi-Rel NPN bipolar transistor 80 V - 1 A

Features

BV_{CEO}	80 V
I_C (max)	1 A
H_{FE} at 10 V - 150 mA	> 100
Operating temperature range	-65°C to +200°C

- Hi-Rel NPN bipolar transistor
- Linear gain characteristics
- ESCC qualified
- European preferred part list - EPPL
- Radiation level: lot specific total dose contact marketing for specified level

Description

The 2N3019AHR is a silicon planar epitaxial NPN transistors in TO-39 package. It is specifically designed for aerospace Hi-Rel applications and ESCC qualified according to the 5201-011 specification. In case of conflict between this datasheet and ESCC detailed specification, the latter prevails.

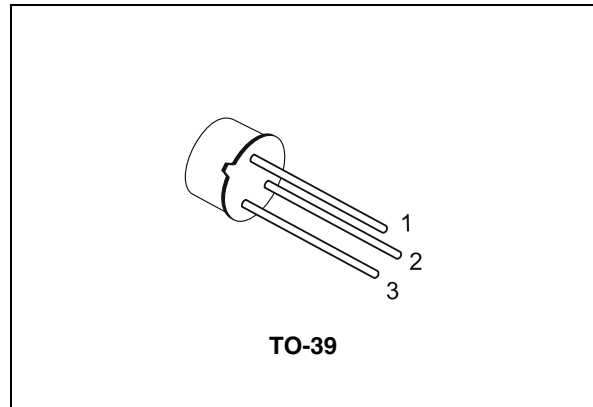


Figure 1. Internal schematic diagram

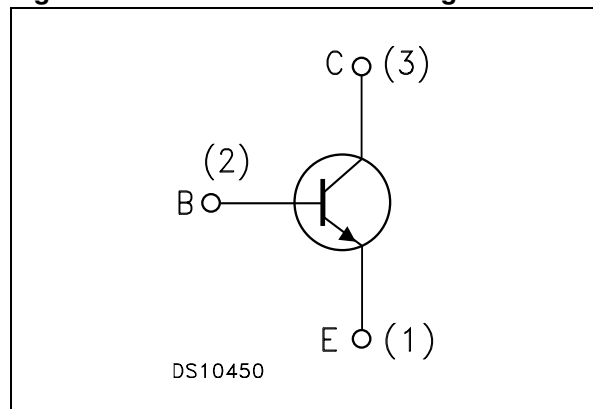


Table 1. Device summary

Order codes	Package	Lead finish	Marking	Type	EPPL	Packaging
2N3019HR	TO-39	Gold Solder Dip	520101103 520101104	ESCC Flight	Yes	Strip pack

1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-base voltage ($I_E = 0$)	140	V
V_{CEO}	Collector-emitter voltage ($I_B = 0$)	80	V
V_{EBO}	Emitter-base voltage ($I_C = 0$)	7	V
I_C	Collector current	1	A
P_{TOT}	Total dissipation at $T_{amb} \leq 25\text{ °C}$	0.8	W
	Total dissipation at $T_c \leq 25\text{ °C}$	5	W
T_{STG}	Storage temperature	-65 to 200	°C
T_J	Max. operating junction temperature	200	°C

Table 3. Thermal data

Symbol	Parameter	Value	Unit
R_{thJC}	Thermal resistance junction-case	max 35	°C/W
R_{thJA}	Thermal resistance junction-ambient	max 218	°C/W

2 Electrical characteristics

$T_{\text{case}} = 25\text{ °C}$ unless otherwise specified

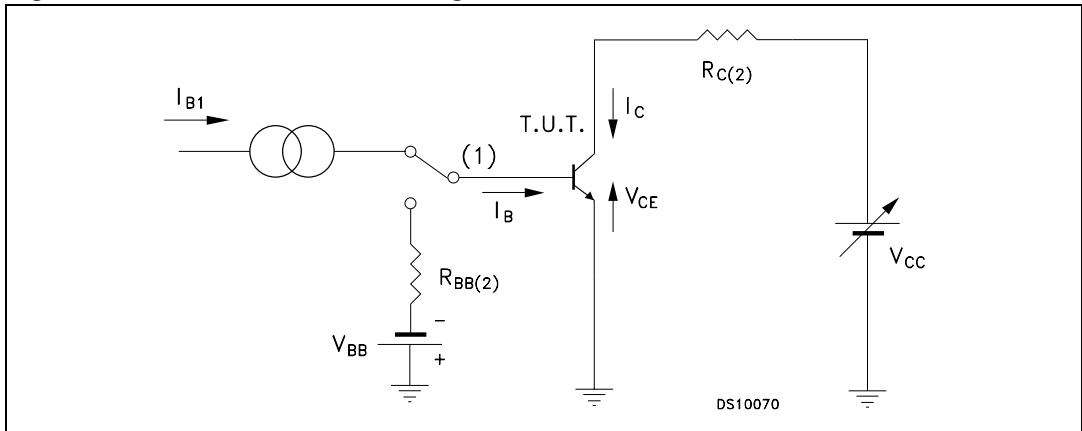
Table 4. Electrical characteristics

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{CES}	Collector cut-off current ($I_{\text{E}} = 0$)	$V_{\text{CB}} = 90\text{ V}$ $V_{\text{CB}} = 90\text{ V}$ $T_{\text{amb}} = 150\text{ °C}$			10 10	nA μA
I_{EBO}	Emitter cut-off current ($I_{\text{C}} = 0$)	$V_{\text{EB}} = 5\text{ V}$			10	nA
$V_{(\text{BR})\text{CBO}}$	Collector-base breakdown voltage ($I_{\text{E}} = 0$)	$I_{\text{C}} = 100\text{ }\mu\text{A}$	140			V
$V_{(\text{BR})\text{CEO}}^{(1)}$	Collector-emitter breakdown voltage ($I_{\text{B}} = 0$)	$I_{\text{C}} = 30\text{ mA}$	80			V
$V_{(\text{BR})\text{EBO}}$	Emitter-base breakdown voltage ($I_{\text{C}} = 0$)	$I_{\text{E}} = 100\text{ }\mu\text{A}$	7			V
$V_{\text{CE}(\text{sat})}^{(1)}$	Collector-emitter saturation voltage	$I_{\text{C}} = 150\text{ mA}$ $I_{\text{B}} = 15\text{ mA}$ $I_{\text{C}} = 500\text{ mA}$ $I_{\text{B}} = 50\text{ mA}$			0.2 0.5	V V
$V_{\text{BE}(\text{sat})}^{(1)}$	Base-emitter saturation voltage	$I_{\text{C}} = 150\text{ mA}$ $I_{\text{B}} = 15\text{ mA}$			1.1	V
$h_{\text{FE}}^{(1)}$	DC current gain	$I_{\text{C}} = 0.1\text{ mA}$ $V_{\text{CE}} = 10\text{ V}$ $I_{\text{C}} = 10\text{ mA}$ $V_{\text{CE}} = 10\text{ V}$ $I_{\text{C}} = 150\text{ mA}$ $V_{\text{CE}} = 10\text{ V}$ $I_{\text{C}} = 500\text{ mA}$ $V_{\text{CE}} = 10\text{ V}$ $I_{\text{C}} = 1\text{ A}$ $V_{\text{CE}} = 10\text{ V}$ $I_{\text{C}} = 150\text{ mA}$ $V_{\text{CE}} = 10\text{ V}$ $T_{\text{amb}} = -65\text{ °C}$	50 90 100 50 15 40		200 300 200	
h_{fe}	Small signal current gain	$V_{\text{CE}} = 10\text{ V}$ $I_{\text{C}} = 50\text{ mA}$ $f = 20\text{ MHz}$	5		20	
h_{fe}	Small signal short circuit forward current transfer ratio	$V_{\text{CE}} = 5\text{ V}$ $I_{\text{C}} = 1\text{ mA}$	80		400	
C_{CBO}	Output capacitance ($I_{\text{E}} = 0$)	$V_{\text{CB}} = 10\text{ V}$ $f = 1\text{ MHz}$			12	pF
C_{IBO}	Input capacitance ($I_{\text{C}} = 0$)	$V_{\text{EB}} = 0.5\text{ V}$ $f = 1\text{ MHz}$			60	pF
NF	Noise figure	$V_{\text{CE}} = 10\text{ V}$ $I_{\text{C}} = 100\text{ }\mu\text{A}$ $R_{\text{G}} = 1\text{ k}\Omega$ Bandwidth = 200 Hz			4	dB
$t_{\text{C}(\text{CB})}$	Collector- base constant time	$V_{\text{CE}} = 10\text{ V}$ $I_{\text{C}} = 10\text{ mA}$ $f = 79.8\text{ MHz}$			400	ps
$t_{\text{on}} + t_{\text{off}}$	Pulse response	$V_{\text{CC}} = 20\text{ V}$ see Figure 4			30	ns

1. Pulsed duration = 300 μs , duty cycle $\leq 2\%$

2.1 Test circuits

Figure 2. Resistive load switching test circuit



1. Fast electronic switch
2. Non-inductive resistor

Figure 3. Circuit for electrical measurement

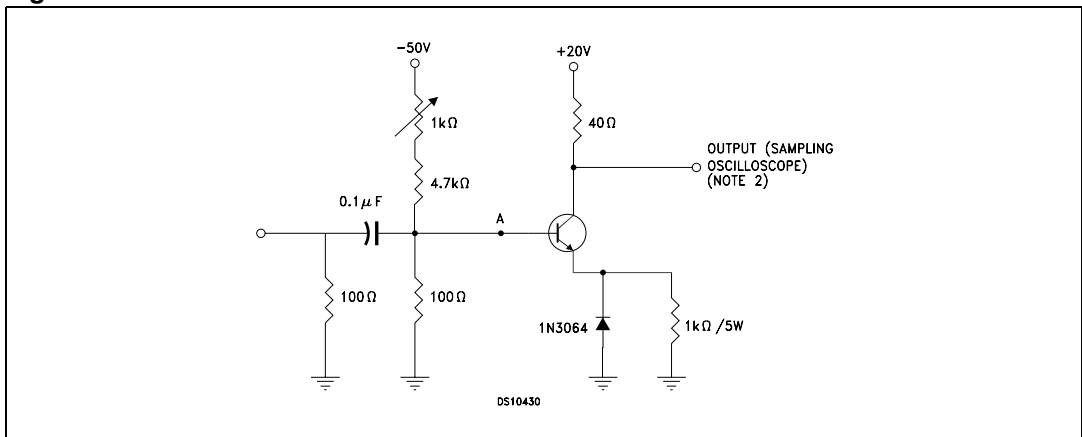
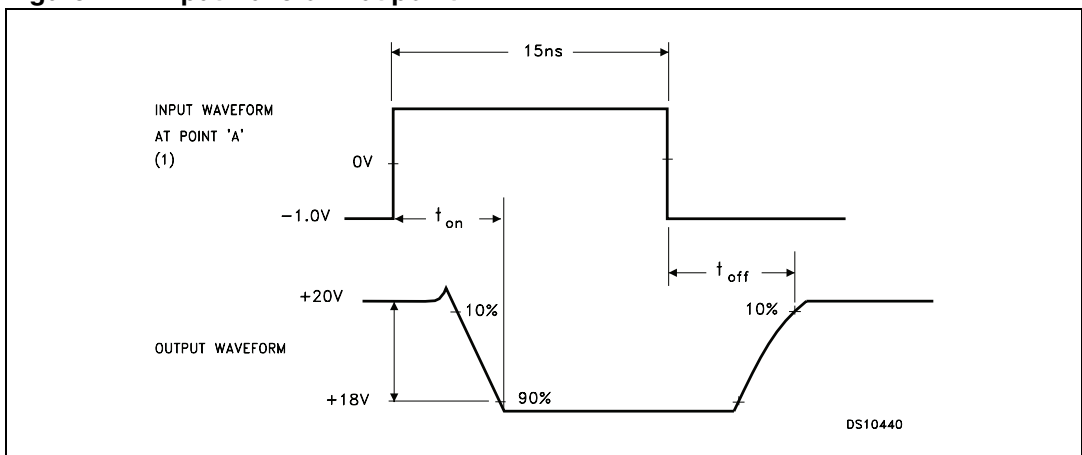


Figure 4. Input waveform at point "A"



1. $t_r \leq 2 \text{ ns}$, duty cycle $\leq 2 \%$, $Z_{IN} = 50 \Omega$
2. Sampling oscilloscope: $Z_{IN} \geq 100 \text{ k}\Omega$, $C_{IN} \leq 12 \text{ pF}$, $t_r \leq 5 \text{ ns}$

3 Package mechanical data

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4 Revision history

Table 5. Document revision history

Date	Revision	Changes
09-Feb-2009	1	Initial release
07-Jan-2010	2	Modified Table 1 on page 1

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